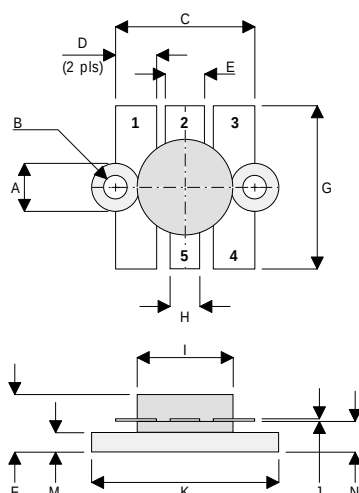


MECHANICAL DATA



DT

PIN 1	SOURCE (COMMON)	PIN 2	GATE
PIN 3	SOURCE (COMMON)	PIN 4	SOURCE (COMMON)
PIN 5	DRAIN		

DIM	mm	Tol.	Inches	Tol.
A	6.35 DIA	0.13	0.250 DIA	0.005
B	3.17 DIA	0.13	0.125 DIA	0.005
C	18.41	0.25	0.725	0.010
D	5.46	0.13	0.215	0.005
E	5.21	0.13	0.205	0.005
F	7.62	MAX	0.300	MAX
G	21.59	0.38	0.850	0.015
H	3.94	0.13	0.155	0.005
I	12.70	0.13	0.500	0.005
J	0.13	0.03	0.005	0.001
K	24.76	0.13	0.975	0.005
M	2.59	0.13	0.102	0.005
N	4.06	0.25	0.160	0.010

GOLD METALLISED MULTI-PURPOSE SILICON DMOS RF FET 30W – 12.5V – 500MHz SINGLE ENDED

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW C_{rss}
- USEFUL P_O AT 1GHz
- LOW NOISE
- HIGH GAIN – 10 dB MINIMUM

APPLICATIONS

- HF/VHF/UHF COMMUNICATIONS
from 1 MHz to 1 GHz

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

P_D	Power Dissipation	117W
BV_{DSS}	Drain – Source Breakdown Voltage	40V
BV_{GSS}	Gate – Source Breakdown Voltage	$\pm 20V$
$I_{D(sat)}$	Drain Current	30A
T_{stg}	Storage Temperature	-65 to $150^{\circ}C$
T_j	Maximum Operating Junction Temperature	$200^{\circ}C$

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV _{DSS} Drain–Source Breakdown Voltage	V _{GS} = 0 I _D = 100mA	40			V
I _{DSS} Zero Gate Voltage Drain Current	V _{DS} = 12.5V V _{GS} = 0			1	mA
I _{GSS} Gate Leakage Current	V _{GS} = 20V V _{DS} = 0			1	μA
V _{GS(th)} Gate Threshold Voltage*	I _D = 10mA V _{DS} = V _{GS}	1		7	V
g _{fs} Forward Transconductance*	V _{DS} = 10V I _D = 3A	2.4			S
G _{PS} Common Source Power Gain	P _O = 30W	10			dB
η Drain Efficiency	V _{DS} = 12.5V I _{DQ} = 0.6A	50			%
VSWR Load Mismatch Tolerance	f = 500MHz	20:1			—
C _{iss} Input Capacitance	V _{DS} = 0 V _{GS} = –5V f = 1MHz			180	pF
C _{oss} Output Capacitance	V _{DS} = 12.5V V _{GS} = 0 f = 1MHz			120	pF
C _{rss} Reverse Transfer Capacitance	V _{DS} = 12.5V V _{GS} = 0 f = 1MHz			12	pF

* Pulse Test: Pulse Duration = 300 μs , Duty Cycle ≤ 2%

HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

THERMAL DATA

R _{THj-case}	Thermal Resistance Junction – Case	Max. 1.5°C / W
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